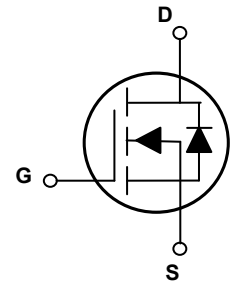
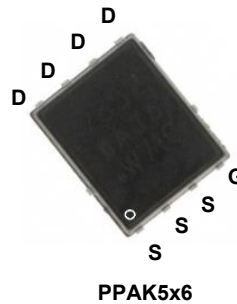


Main Product Characteristics

BV_{DSS}	60V
$R_{DS(ON)}$	16m Ω (Max)
I_D	50A



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFP6016 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, @ Steady-State ¹ ($T_c=25^\circ\text{C}$)	I_D	50	A
Continuous Drain Current, @ Steady-State ($T_c=100^\circ\text{C}$)		32	A
Pulsed Drain Current ²	I_{DM}	200	A
Power Dissipation ($T_c=25^\circ\text{C}$)	P_D	60	W
Linear Derating Factor ($T_c=25^\circ\text{C}$)		0.48	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy ³	E_{AS}	49	mJ
Junction-to-Case	$R_{\theta JC}$	2.10	$^\circ\text{C}/\text{W}$
Junction-to-Ambient (PCB Mounted, Steady-State) ⁴	$R_{\theta JA}$	62.0	$^\circ\text{C}/\text{W}$
Operating Junction Temperature Range	T_J	-55 to +150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	μA
		$T_J=125^\circ\text{C}$	-	-	20	
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS}=\pm 20V$	-	-	± 100	nA
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	12	16	m Ω
		$V_{GS}=4.5V, I_D=15A$	-	15	22	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.1	1.6	2.9	V
Dynamic and Switching Characteristics						
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=30V$ $F=1\text{MHz}$	-	2200	-	μF
Output Capacitance	C_{oss}		-	140	-	
Reverse Transfer Capacitance	C_{rss}		-	70	-	
Total Gate Charge	Q_g	$I_D=20A, V_{DS}=30V,$ $V_{GS}=10V$	-	48	-	nC
Gate-to-Source Charge	Q_{gs}		-	9.2	-	
Gate-to-Drain ("Miller") Charge	Q_{gd}		-	10	-	
Turn-on Delay Time	$t_{d(on)}$	$V_{GS}=10V, V_{DS}=30V,$ $I_D=20A, R_{GEN}=3\Omega$	-	11	-	nS
Rise Time	t_r		-	26	-	
Turn-Off Delay Time	$t_{d(off)}$		-	87	-	
Fall Time	t_f		-	75	-	
Gate Resistance	R_g	$F=1\text{MHz}$	-	2.2	-	Ω
Source-Drain Ratings and Characteristics						
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode.	-	-	50	A
Pulsed Source Current (Body Diode)	I_{SM}		-	-	200	A
Diode Forward Voltage	V_{SD}	$I_S=20A, V_{GS}=0V$	-	1.0	1.2	V
Reverse Recovery Time	t_{rr}	$T_J=25^\circ\text{C}, I_F=20A,$ $di/dt=100A/\mu s$		14		ns
Reverse Recovery Charge	Q_{rr}				16.5	

Notes

1. Pulse test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
2. Repetitive rating; pulse width limited by max. junction temperature.
3. $L=0.5\text{mH}, V_{DD}=30V, R_G=25\Omega, T_J=25^\circ\text{C}$.
4. Device mounted on FR-4 PCB, 1inch x 0.85inch x 0.062inch.

Typical Electrical and Thermal Characteristic Curves

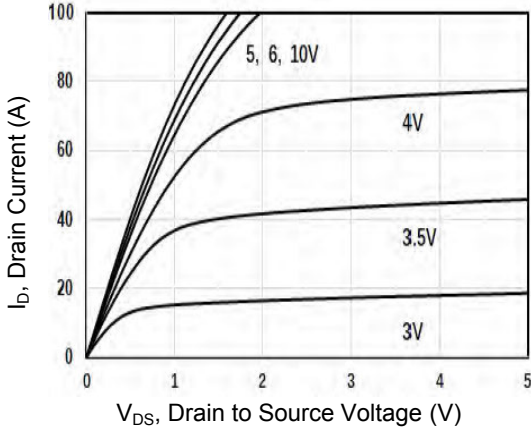


Figure 1. Typical Output Characteristics

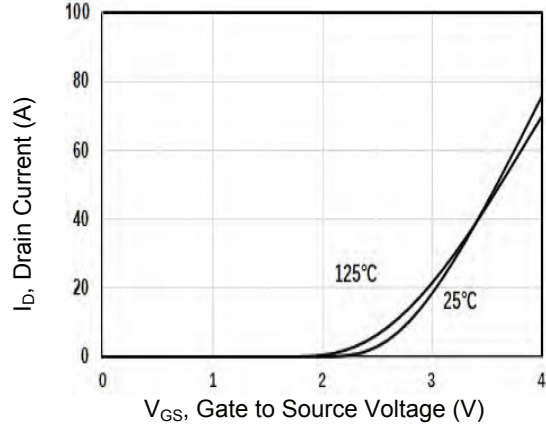


Figure 2. Transfer Characteristics

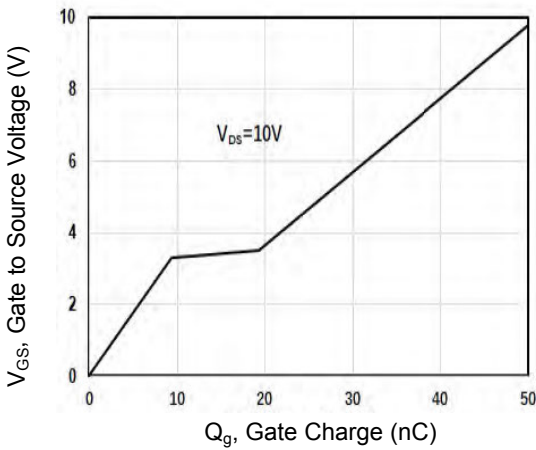


Figure 3. Gate Charge Characteristics

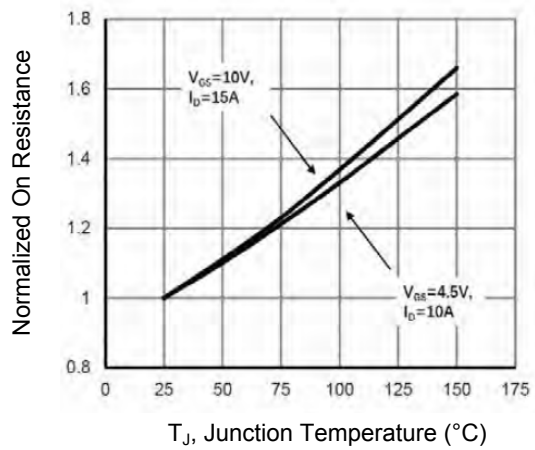


Figure 4. Normalized $R_{DS(ON)}$ vs. T_J

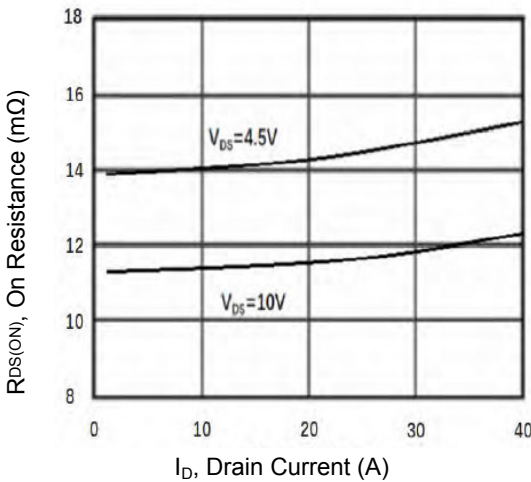


Figure 5. $R_{DS(ON)}$ vs. Drain Current

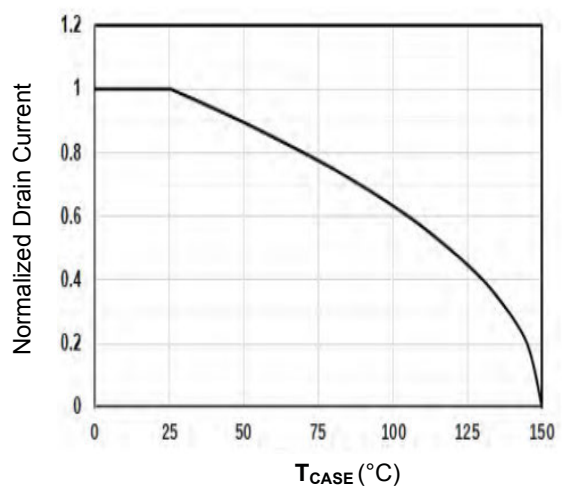


Figure 6. Normalized Current vs. Junction Temperature

Typical Electrical and Thermal Characteristic Curves

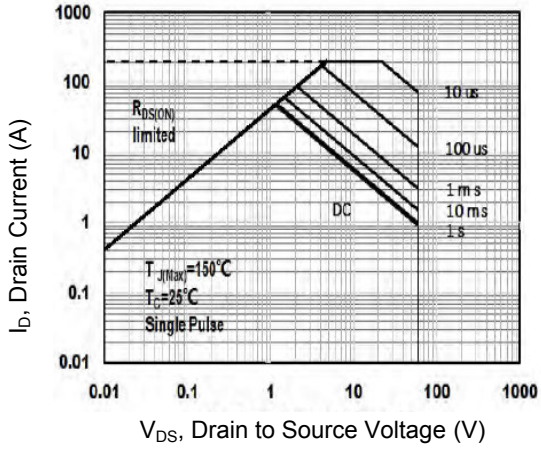


Figure 7. Safe Operation Area

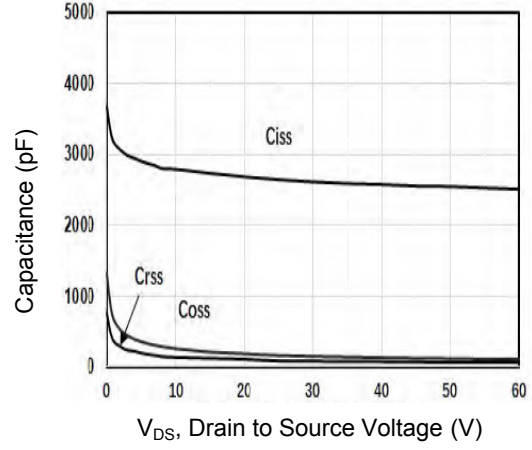
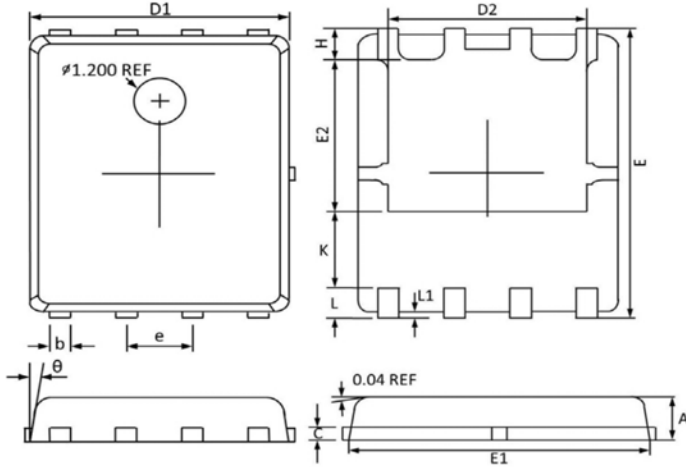


Figure 8. Capacitance Characteristics

Package Outline Dimensions (PPAK5x6)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.800	1.100	0.031	0.043
b	0.330	0.510	0.013	0.020
C	0.200	0.300	0.008	0.012
D1	4.800	5.100	0.189	0.201
D2	3.610	4.100	0.142	0.161
E	5.900	6.200	0.232	0.244
E1	5.700	5.900	0.224	0.232
E2	3.350	3.780	0.132	0.149
e	1.27BSC		0.05BSC	
H	0.410	0.700	0.016	0.028
K	1.100	1.500	0.043	0.059
L	0.510	0.710	0.020	0.028
L1	0.060	0.200	0.002	0.008
θ	0°	12°	0°	12°